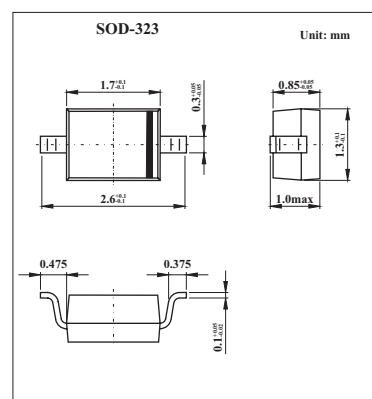


Silicon RF Switching Diode

BAR65-03W

■ Features

- Low loss, low capacitance PIN-diode
- Band switch for TV-tuners
- Series diode for mobile communications transmit-receive switch

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Operating temperature range	T_{op}	-55 to +125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 20\text{ V}, T_a = 25^\circ\text{C}$			20	nA
Forward voltage	V_F	$I_F = 100\text{ mA}$		0.93	1	V
Diode capacitance	C_T	$V_R = 1\text{ V}, f = 1\text{ MHz}$		0.6	0.9	pF
		$V_R = 3\text{ V}, f = 1\text{ MHz}$		0.57	0.8	
Forward resistance	r_f	$I_F = 5\text{ mA}, f = 100\text{ MHz}$		0.65	0.95	Ω
		$I_F = 10\text{ mA}, f = 100\text{ MHz}$		0.56	0.9	
Series inductance	L_s			1.8		nH

■ Marking

Marking	blue M
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